HALL EFFECT MEASUREMENT SYSTEM

FYTRONIX HE-9000

FYTRONIX Hall effect systems measure the electrical properties of semiconductor materials.

TECHNICAL SPECIFICATIONS

The device is compact and suitable for benchtop use.

Resistance (resistance) measuring range: 10^{-4} and 10^{7} (Ohm.cm)

Carrier density: 10^{7} -10^{2l} cm^{-3}

Mobility measuring range: 10^{7} (cm^{2}/Volt.s).

Carrier concentration: 10^{7}-10^{21} cm^{-3}

Current source range: 1 nA to 200 mA

Output voltage: 12V

Magnetic field: 0.5 Tesla

Hall voltage value: at least 1 mV

Sample measurement area: Measurement area up to 20x20 mm

Hall effect switcher

Measured parameters

Sheet resistance, resistivity,

Conductivity

Resistivity

Hall coefficient

Magneto resistance

These parameters are displayed on the computer screen via software.

Measurements made with software

Hall effect measurements

Current-voltage measurements (I-V)

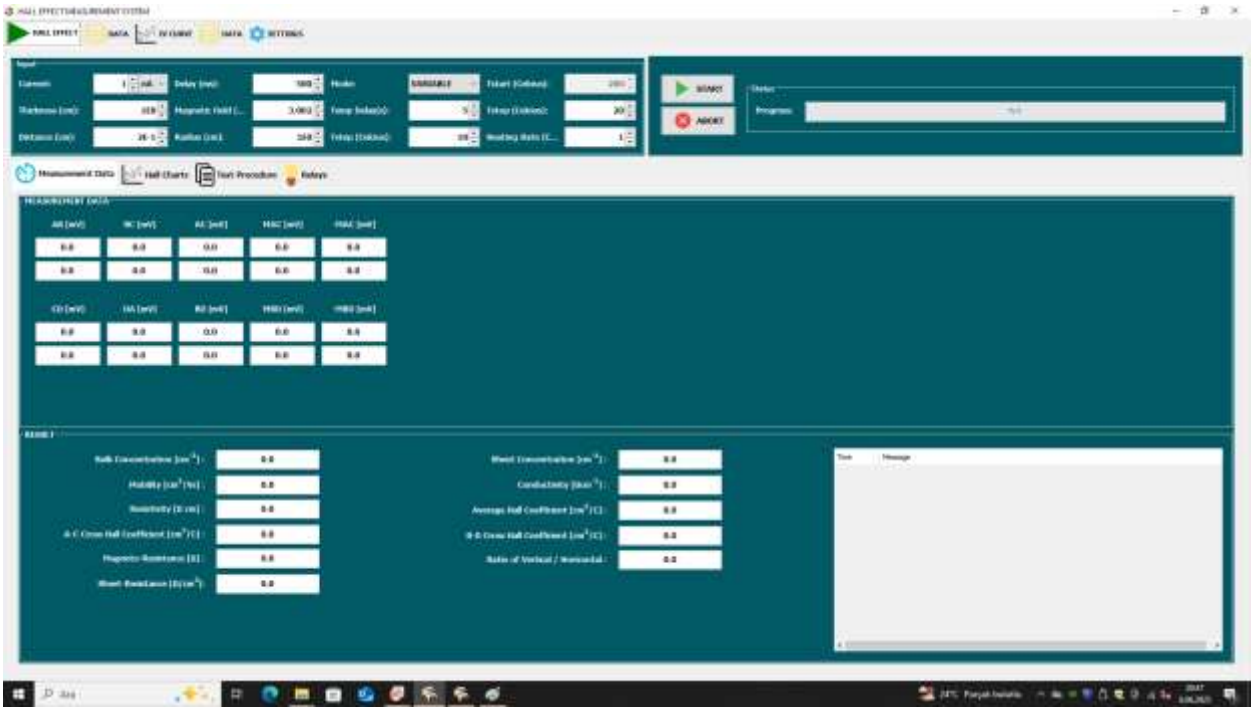
Current-Resistance measurements (I-R)

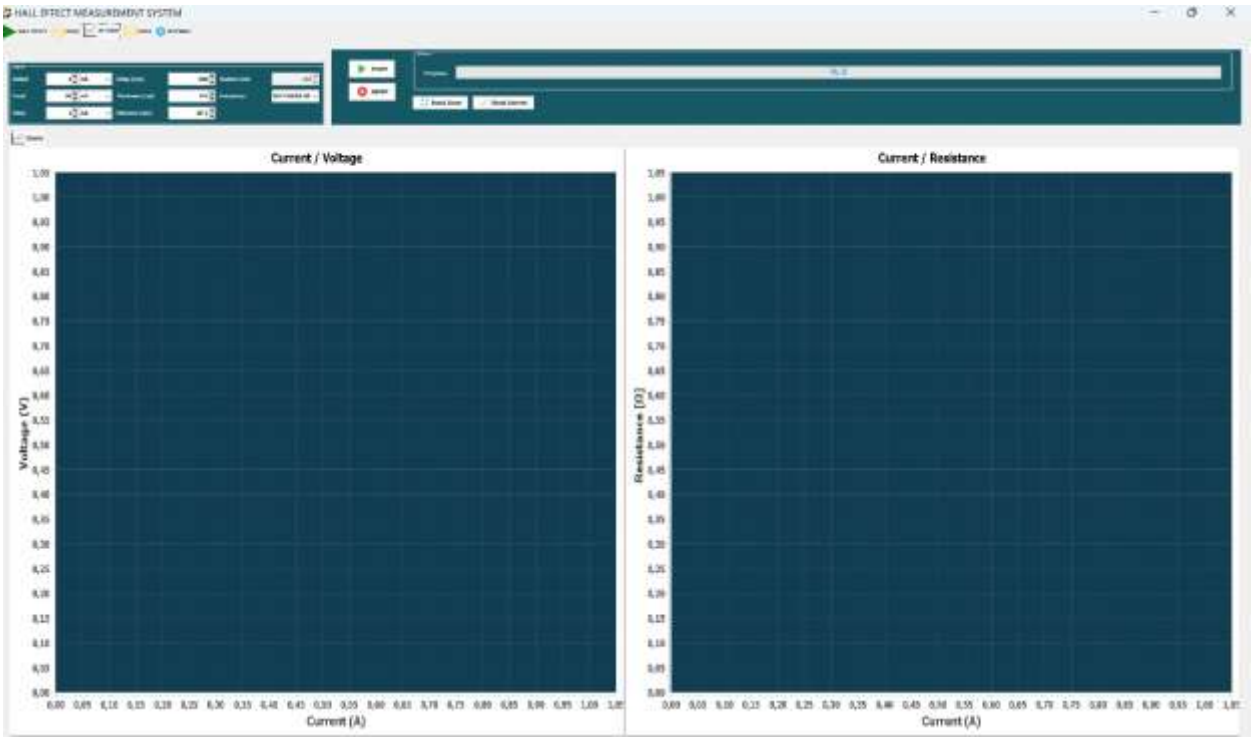
Sample holder: For samples up to 20x2O mm

Reference sample

Direct attachment of the sample to the sample holder with pins

Preparing contacts with silver paint

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Current / Voltage
Voltage (V)
Current (A)
Current / Resistance
Resistance (Ω)
Current (A)